



Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

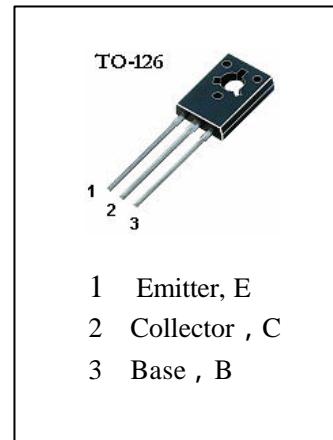
HSBD377

APPLICATIONS

Medium Power Linear switching Applications

ABSOLUTE MAXIMUM RATINGS (T_a=25)

T _{stg}	—Storage Temperature.....	-55~150
T _j	—Junction Temperature.....	150
P _c	—Collector Dissipation (T _c =25)	25W
V _{CBO}	—Collector-Base Voltage.....	75V
V _{CEO}	—Collector-Emitter Voltage.....	60V
V _{EBO}	—Emitter-Base Voltage.....	5V
I _c	—Collector Current(Pulse)	3A
I _c	—Collector Current(DC).....	2A
I _b	—Base Current.....	1A



ELECTRICAL CHARACTERISTICS (T_a=25)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
I _{CBO}	Collector Cut-off Current			2	μ A	V _{CB} =60V, I _E =0
I _{EBO}	Emitter Cut-off Current			100	μ A	V _{EB} =5V, I _C =0
*H _{FE} (1)	DC Current Gain	40		375		V _{CE} =2V, I _C =150mA
*H _{FE} (2)	DC Current Gain	20				V _{CE} =2V, I _C =1A
*V _{CESAT}	Collector- Emitter Saturation Voltage			1	V	I _C =1A, I _B =0.1A
*V _{BE(on)}	Base-Emitter On Voltage			1.5	V	V _{CE} =2V, I _C =1A
V _{CEO(sus)}	Collector-Emitter Sustaining Voltage	60			V	I _C =100mA, I _B =0
BV _{CBO}	Collector-Base Breakdown Voltage	75			V	I _C =100 μ A, I _E =0
t _{ON}	Turn-On Time		50		nS	V _{CC} =30V, I _C =0.5A
t _{OFF}	Turn-Off Time		500		nS	

* Pulse Test: PW=350 μ S, Duty Cycle=2% Pulsed

h_{FE(3)} Classification

Classification	6	10	16	25
h _{FE(3)}	40~100	63~160	100~250	150~375